

iCE40[™] LP/HX Family Data Sheet

DS1040 Version 3.1, March 2015



iCE40 LP/HX Family Data Sheet Introduction

February 2014

Features

- Flexible Logic Architecture
 - Five devices with 384 to 7,680 LUT4s and 10 to 206 I/Os
- Ultra Low Power Devices
 - Advanced 40 nm low power process
 - As low as 21 µA standby power
 - Programmable low swing differential I/Os

Embedded and Distributed Memory

- Up to 128 kbits sysMEM[™] Embedded Block RAM
- Pre-Engineered Source Synchronous I/O
- DDR registers in I/O cells
- High Current LED Drivers
 - Three High Current Drivers used for three different LEDs or one RGB LED
- High Performance, Flexible I/O Buffer
 - Programmable sysIO[™] buffer supports wide range of interfaces:
 - LVCMOS 3.3/2.5/1.8
 - LVDS25E, subLVDS

- Schmitt trigger inputs, to 200 mV typical hysteresis
- Programmable pull-up mode
- Flexible On-Chip Clocking
 - · Eight low-skew global clock resources
 - Up to two analog PLLs per device
- Flexible Device Configuration
 - SRAM is configured through:
 - Standard SPI Interface
 - Internal Nonvolatile Configuration Memory (NVCM)
- Broad Range of Package Options
 - WLCSP, QFN, VQFP, TQFP, ucBGA, caBGA, and csBGA package options
 - Small footprint package options — As small as 1.40 mm x 1.48 mm
 - Advanced halogen-free packaging

Part Number		LP384	LP640	LP1K	LP4K	LP8K	HX1K	HX4K	HX8K
Logic Cells (LUT + Flip-Flop))	384	640	1,280	3,520	7,680	1,280	3,520	7,680
RAM4K Memory Blocks		0	8	16	20	32	16	20	32
RAM4K RAM bits		0	32K	64K	80K	128K	64K	80K	128K
Phase-Locked Loops (PLLs)		0	0	1 ¹	2 ²	2 ²	1 ¹	2	2
Maximum Programmable I/C	Pins	63	25	95	167	178	95	95	206
Maximum Differential Input F	Pairs	8	3	12	20	23	11	12	26
High Current LED Drivers		0	3	3	0	0	0	0	0
Package	Code		•	Programn	nable I/O:	Max Inputs	(LVDS25)		
16 WLCSP (1.40 mm x 1.48 mm, 0.35 mm)	SWG16		10(0)	10(0)					
32 QFN (5 mm x 5 mm, 0.5 mm)	SG32	21(3)							
36 ucBGA (2.5 mm x 2.5 mm, 0.4 mm)	CM36	25(3)		25(3) ¹					
49 ucBGA (3 mm x 3 mm, 0.4 mm)	CM49	37(6)		35(5) ¹					
81 ucBGA (4 mm x 4 mm, 0.4 mm)	CM81			63(8)	63(9) ²	63(9) ²			
81 csBGA (5 mm x 5 mm, 0.5 mm)	CB81			62(9) ¹					

Table 1-1. iCE40 Family Selection Guide

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Table 1-1. iCE40 Famil	v Selection Guide	(continued)
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84 QFN (7 mm x 7 mm, 0.5 mm)	QN84		67(7) ¹					
100 VQFP (14 mm x 14 mm, 0.5 mm)	VQ100					72(9) ¹		
121 ucBGA (5 mm x 5 mm, 0.4 mm)	CM121		95(12)	93(13)	93(13)			
121 csBGA (6 mm x 6 mm, 0.5 mm)	CB121		92(12)					
132 csBGA (8 mm x 8 mm, 0.5 mm)	CB132					95(11)	95(12)	95(12)
144 TQFP (20 mm x 20 mm, 0.5 mm)	TQ144					96(12)	107(14)	
225 ucBGA (7 mm x 7 mm, 0.4 mm)	CM225			178(23)	178(23)			178(23)
256-ball caBGA (14 mm x 14 mm, 0.8 mm)	CT256							206(26)

1. No PLL available on the 16 WLCSP, 36 ucBGA, 81 csBGA, 84 QFN and 100 VQFP packages.

2. Only one PLL available on the 81 ucBGA package.

3. High Current I/Os only available on the 16 WLCSP package.

Introduction

The iCE40 family of ultra-low power, non-volatile FPGAs has five devices with densities ranging from 384 to 7680 Look-Up Tables (LUTs). In addition to LUT-based, low-cost programmable logic, these devices feature Embedded Block RAM (EBR), Non-volatile Configuration Memory (NVCM) and Phase Locked Loops (PLLs). These features allow the devices to be used in low-cost, high-volume consumer and system applications. Select packages offer High-Current drivers that are ideal to drive three white LEDs, or one RGB LED.

The iCE40 devices are fabricated on a 40 nm CMOS low power process. The device architecture has several features such as programmable low-swing differential I/Os and the ability to turn off on-chip PLLs dynamically. These features help manage static and dynamic power consumption, resulting in low static power for all members of the family. The iCE40 devices are available in two versions – ultra low power (LP) and high performance (HX) devices.

The iCE40 FPGAs are available in a broad range of advanced halogen-free packages ranging from the space saving 1.40x1.48 mm WLCSP to the PCB-friendly 20x20 mm TQFP. Table 1-1 shows the LUT densities, package and I/O options, along with other key parameters.

The iCE40 devices offer enhanced I/O features such as pull-up resistors. Pull-up features are controllable on a "per-pin" basis.

The iCE40 devices also provide flexible, reliable and secure configuration from on-chip NVCM. These devices can also configure themselves from external SPI Flash or be configured by an external master such as a CPU.

Lattice provides a variety of design tools that allow complex designs to be efficiently implemented using the iCE40 family of devices. Popular logic synthesis tools provide synthesis library support for iCE40. Lattice design tools use the synthesis tool output along with the user-specified preferences and constraints to place and route the design in the iCE40 device. These tools extract the timing from the routing and back-annotate it into the design for timing verification.

Lattice provides many pre-engineered IP (Intellectual Property) modules, including a number of reference designs, licensed free of charge, optimized for the iCE40 FPGA family. By using these configurable soft core IP cores as standardized blocks, users are free to concentrate on the unique aspects of their design, increasing their productivity.



iCE40 LP/HX Family Data Sheet Architecture

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Architecture Overview

The iCE40 family architecture contains an array of Programmable Logic Blocks (PLB), sysCLOCK[™] PLLs, Nonvolatile Programmable Configuration Memory (NVCM) and blocks of sysMEM[™] Embedded Block RAM (EBR) surrounded by Programmable I/O (PIO). Figure 2-1 shows the block diagram of the iCE40LP/HX1K device.

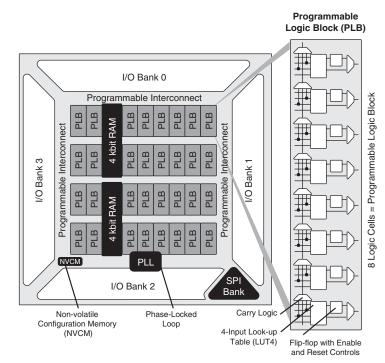


Figure 2-1. iCE40LP/HX1K Device, Top View

The logic blocks, Programmable Logic Blocks (PLB) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each column has either logic blocks or EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PLB contains the building blocks for logic, arithmetic, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the iCE40 family, there are up to four independent sysIO banks. Note on some packages V_{CCIO} banks are tied together. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large 4 kbit, dedicated fast memory blocks. These blocks can be configured as RAM, ROM or FIFO.

The iCE40 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

Every device in the family has a SPI port that supports programming and configuration of the device. The iCE40 includes on-chip, Nonvolatile Configuration Memory (NVCM).

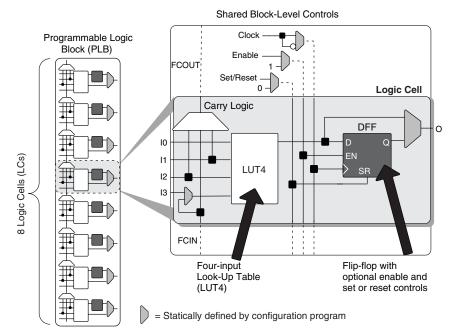
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PLB Blocks

The core of the iCE40 device consists of Programmable Logic Blocks (PLB) which can be programmed to perform logic and arithmetic functions. Each PLB consists of eight interconnected Logic Cells (LC) as shown in Figure 2-2. Each LC contains one LUT and one register.

Figure 2-2. PLB Block Diagram



Logic Cells

Each Logic Cell includes three primary logic elements shown in Figure 2-2.

- A four-input Look-Up Table (LUT4) builds any combinational logic function, of any complexity, requiring up to four inputs. Similarly, the LUT4 element behaves as a 16x1 Read-Only Memory (ROM). Combine and cascade multiple LUT4s to create wider logic functions.
- A 'D'-style Flip-Flop (DFF), with an optional clock-enable and reset control input, builds sequential logic functions. Each DFF also connects to a global reset signal that is automatically asserted immediately following device configuration.
- Carry Logic boosts the logic efficiency and performance of arithmetic functions, including adders, subtracters, comparators, binary counters and some wide, cascaded logic functions.

Function	Туре	Signal Names	Description
Input	Data signal	10, 11, 12, 13	Inputs to LUT4
Input	Control signal	Enable	Clock enable shared by all LCs in the PLB
Input	Control signal	Set/Reset ¹	Asynchronous or synchronous local set/reset shared by all LCs in the PLB.
Input	Control signal	Clock	Clock one of the eight Global Buffers, or from the general-purpose interconnects fabric shared by all LCs in the PLB
Input	Inter-PLB signal	FCIN	Fast carry in
Output	Data signals	0	LUT4 or registered output
Output	Inter-PFU signal	FCOUT	Fast carry out

Table 2-1. Logic Cell Signal Descriptions

1. If Set/Reset is not used, then the flip-flop is never set/reset, except when cleared immediately after configuration.



Routing

There are many resources provided in the iCE40 devices to route signals individually with related control signals. The routing resources consist of switching circuitry, buffers and metal interconnect (routing) segments.

The inter-PLB connections are made with three different types of routing resources: Adjacent (spans two PLBs), x4 (spans five PLBs) and x12 (spans thirteen PLBs). The Adjacent, x4 and x12 connections provide fast and efficient connections in the diagonal, horizontal and vertical directions.

The design tool takes the output of the synthesis tool and places and routes the design.

Clock/Control Distribution Network

Each iCE40 device has eight global inputs, two pins on each side of the device. Note that not all GBINs are available in all packages.

These global inputs can be used as high fanout nets, clock, reset or enable signals. The dedicated global pins are identified as GBIN[7:0] and the global buffers are identified as-GBUF[7:0]. These eight inputs may be used as general purpose I/O if they are not used to drive the clock nets. Global buffer GBUF7 in I/O Bank 3 also provides an optional direct LVDS25 or subLVDS differential clock input.

Table 2-2 lists the connections between a specific global buffer and the inputs on a PLB. All global buffers optionally connect to the PLB CLK input. Any four of the eight global buffers can drive logic inputs to a PLB. Even-numbered global buffers optionally drive the Set/Reset input to a PLB. Similarly, odd-numbered buffers optionally drive the PLB clock-enable input.

Global Buffer	LUT Inputs	Clock	Clock Enable	Reset
GBUF0		Yes	Yes	
GBUF1		Yes		Yes
GBUF2		Yes	Yes	
GBUF3	Yes, any 4 of 8	Yes		Yes
GBUF4	GBUF Inputs	Yes	Yes	
GBUF5		Yes		Yes
GBUF6		Yes	Yes	
GBUF7		Yes		Yes

Table 2-2. Global Buffer (GBUF) Connections to Programmable Logic Blocks

The maximum frequency for the global buffers are shown in the iCE40 External Switching Characteristics tables later in this document.

Global Hi-Z Control

The global high-impedance control signal, GHIZ, connects to all I/O pins on the iCE40 device. This GHIZ signal is automatically asserted throughout the configuration process, forcing all user I/O pins into their high-impedance state.



Global Reset Control

The global reset control signal connects to all PLB and PIO flip-flops on the iCE40 device. The global reset signal is automatically asserted throughout the configuration process, forcing all flip-flops to their defined wake-up state. For PLB flip-flops, the wake-up state is always reset, regardless of the PLB flip-flop primitive used in the application.

sysCLOCK Phase Locked Loops (PLLs)

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. The iCE40 devices have one or more sys-CLOCK PLLs. REFERENCECLK is the reference frequency input to the PLL and its source can come from an external I/O pin or from internal routing. EXTFEEDBACK is the feedback signal to the PLL which can come from internal routing or an external I/O pin. The feedback divider is used to multiply the reference frequency and thus synthesize a higher frequency clock output.

The PLLOUT output has an output divider, thus allowing the PLL to generate different frequencies for each output. The output divider can have a value from 1 to 6. The PLLOUT outputs can all be used to drive the iCE40 global clock network directly or general purpose routing resources can be used.

The LOCK signal is asserted when the PLL determines it has achieved lock and de-asserted if a loss of lock is detected. A block diagram of the PLL is shown in Figure 2-3.

The timing of the device registers can be optimized by programming a phase shift into the PLLOUT output clock which will advance or delay the output clock with reference to the REFERENCECLK clock. This phase shift can be either programmed during configuration or can be adjusted dynamically. In dynamic mode, the PLL may lose lock after a phase adjustment on the output used as the feedback source and not relock until the t_{LOCK} parameter has been satisfied.

For more details on the PLL, see TN1251, iCE40 sysCLOCK PLL Design and Usage Guide.

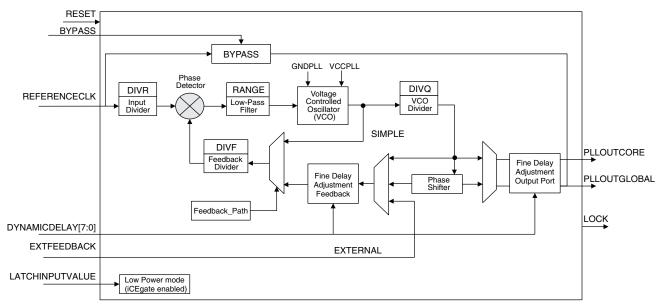


Figure 2-3. PLL Diagram

Table 2-3 provides signal descriptions of the PLL block.



Table 2-3. PLL Signal Descriptions

Signal Name	Direction	Description
REFERENCECLK	Input	Input reference clock
BYPASS	Input	When FEEDBACK_PATH is set to SIMPLE, the BYPASS control selects which clock sig- nal connects to the PLLOUT output.
DTFASS	mput	0 = PLL generated signal 1 = REFERENCECLK
EXTFEEDBACK	Input	External feedback input to PLL. Enabled when the FEEDBACK_PATH attribute is set to EXTERNAL.
DYNAMICDELAY[3:0]	Input	Fine delay adjustment control inputs. Enabled when DELAY_ADJUSTMENT_MODE is set to DYNAMIC.
LATCHINPUTVALUE	Input	When enabled, forces the PLL into low-power mode; PLL output is held static at the last input clock value. Set ENABLE ICEGATE_PORTA and PORTB to '1' to enable.
PLLOUTGLOBAL	Output	Output from the Phase-Locked Loop (PLL). Drives a global clock network on the FPGA. The port has optimal connections to global clock buffers GBUF4 and GBUF5.
PLLOUTCORE	Output	Output clock generated by the PLL, drives regular FPGA routing. The frequency gener- ated on this output is the same as the frequency of the clock signal generated on the PLLOUTLGOBAL port.
LOCK	Output	When High, indicates that the PLL output is phase aligned or locked to the input reference clock.
RESET	Input	Active low reset.

sysMEM Embedded Block RAM Memory

Larger iCE40 device includes multiple high-speed synchronous sysMEM Embedded Block RAMs (EBRs), each 4 kbit in size. This memory can be used for a wide variety of purposes including data buffering, and FIFO.

sysMEM Memory Block

The sysMEM block can implement single port, pseudo dual port, or FIFO memories with programmable logic resources. Each block can be used in a variety of depths and widths as shown in Table 2-4.

Block RAM Configuration	Block RAM Configuration and Size	WADDR Port Size (Bits)	WDATA Port Size (Bits)	RADDR Port Size (Bits)	RDATA Port Size (Bits)	MASK Port Size (Bits)
SB_RAM256x16 SB_RAM256x16NR SB_RAM256x16NW SB_RAM256x16NRNW	256x16 (4K)	8 [7:0]	16 [15:0]	8 [7:0]	16 [15:0]	16 [15:0]
SB_RAM512x8 SB_RAM512x8NR SB_RAM512x8NW SB_RAM512x8NRNW	512x8 (4K)	9 [8:0]	8 [7:0]	9 [8:0]	8 [7:0]	No Mask Port
SB_RAM1024x4 SB_RAM1024x4NR SB_RAM1024x4NW SB_RAM1024x4NRNW	1024x4 (4K)	10 [9:0]	4 [3:0]	10 [9:0]	4 [3:0]	No Mask Port
SB_RAM2048x2 SB_RAM2048x2NR SB_RAM2048x2NW SB_RAM2048x2NRNW	2048x2 (4K)	11 [10:0]	2 [1:0]	11 [10:0]	2 [1:0]	No Mask Port

Table 2-4. sysMEM Block Configurations¹

1. For iCE40 EBR primitives with a negative-edged Read or Write clock, the base primitive name is appended with a 'N' and a 'R' or 'W' depending on the clock that is affected.



RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Note the sysMEM Embedded Block RAM Memory address 0 cannot be initialized.

Memory Cascading

Larger and deeper blocks of RAM can be created using multiple EBR sysMEM Blocks.

RAM4k Block

Figure 2-4 shows the 256x16 memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array.

Figure 2-4. sysMEM Memory Primitives

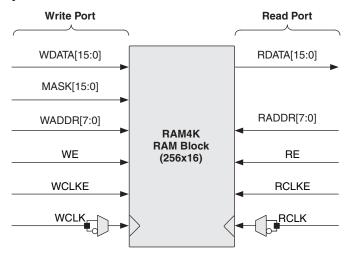


Table 2-5. EBR Signal Descriptions

Signal Name	Direction	Description
WDATA[15:0]	Input	Write Data input.
MASK[15:0]	Input	Masks write operations for individual data bit-lines. 0 = write bit; 1 = don't write bit
WADDR[7:0]	Input	Write Address input. Selects one of 256 possible RAM locations.
WE	Input	Write Enable input.
WCLKE	Input	Write Clock Enable input.
WCLK	Input	Write Clock input. Default rising-edge, but with falling-edge option.
RDATA[15:0]	Output	Read Data output.
RADDR[7:0]	Input	Read Address input. Selects one of 256 possible RAM locations.
RE	Input	Read Enable input.
RCLKE	Input	Read Clock Enable input.
RCLK	Input	Read Clock input. Default rising-edge, but with falling-edge option.

For further information on the sysMEM EBR block, please refer to TN1250, Memory Usage Guide for iCE40 Devices.



syslO

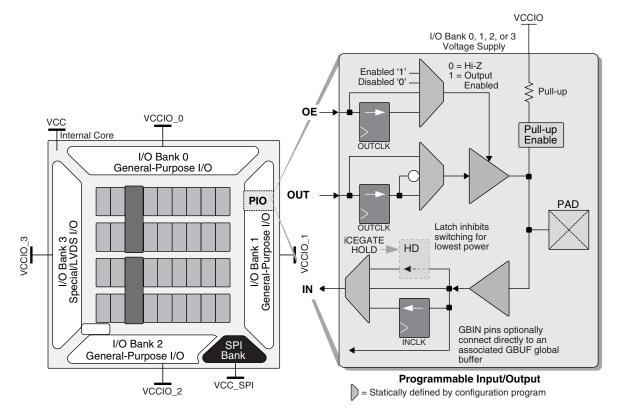
Buffer Banks

iCE40 devices have up to four I/O banks with independent V_{CCIO} rails with an additional configuration bank V_{CC} SPI for the SPI I/Os.

Programmable I/O (PIO)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. The PIOs are placed on all four sides of the device.

Figure 2-5. I/O Bank and Programmable I/O Cell



The PIO contains three blocks: an input register block, output register block iCEgate[™] and tri-state register block. To save power, the optional iCEgate[™] latch can selectively freeze the state of individual, non-registered inputs within an I/O bank. Note that the freeze signal is common to the bank. These blocks can operate in a variety of modes along with the necessary clock and selection logic.

Input Register Block

The input register blocks for the PIOs on all edges contain registers that can be used to condition high-speed interface signals before they are passed to the device core. In Generic DDR mode, two registers are used to sample the data on the positive and negative edges of the system clock signal, creating two data streams.

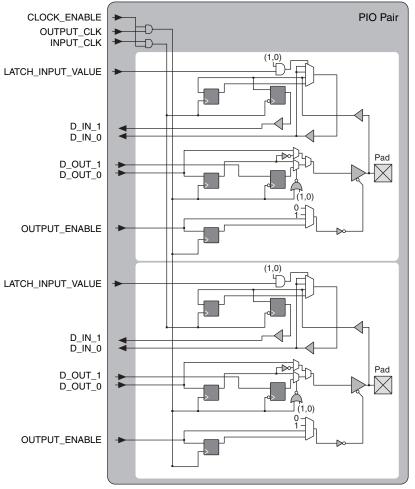
Output Register Block

The output register block can optionally register signals from the core of the device before they are passed to the sysIO buffers. In Generic DDR mode, two registers are used to capture the data on the positive and negative edge of the system clock and then muxed creating one data stream.

Figure 2-6 shows the input/output register block for the PIOs.



Figure 2-6. iCE I/O Register Block Diagram



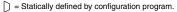


Table 2-6. PIO Signal List

Pin Name	I/O Type	Description
OUTPUT_CLK	Input	Output register clock
CLOCK_ENABLE	Input	Clock enable
INPUT_CLK	Input	Input register clock
OUTPUT_ENABLE	Input	Output enable
D_OUT_0/1	Input	Data from the core
D_IN_0/1	Output	Data to the core
LATCH_INPUT_VALUE	Input	Latches/holds the Input Value

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS and LVDS25.

High Current LED Drivers combine three sysIO buffers together. This allows for programmable drive strength. This also allows for high current drivers that are ideal to drive three white LEDs, or one RGB LED. Each bank is capable of supporting multiple I/O standards including single-ended LVCMOS buffers and differential LVDS25E output buf-



fers. Bank 3 additionally supports differential LVDS25 input buffers. Each sysIO bank has its own dedicated power supply.

Typical I/O Behavior During Power-up

The internal power-on-reset (POR) signal is deactivated when V_{CC} , V_{CCIO_2} , V_{PP_2V5} , and V_{CC_SP1} have reached the level defined in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user's responsibility to ensure that all V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. The default configuration of the I/O pins in a device prior to configuration is tri-stated with a weak pull-up to V_{CCIO} . The I/O pins will maintain the pre-configuration state until V_{CC} and V_{CCIO} (for I/O banks containing configuration I/Os) have reached levels, at which time the I/Os will take on the software user-configured settings only after a proper download/configuration. Unused IOs are automatically blocked and the pullup termination is disabled.

Supported Standards

The iCE40 sysIO buffer supports both single-ended and differential input standards. The single-ended standard supported is LVCMOS. The buffer supports the LVCMOS 1.8, 2.5, and 3.3 V standards. The buffer has individually configurable options for bus maintenance (weak pull-up or none). The High Current output buffer have individually configurable options for drive strength.

Table 2-7 and Table 2-8 show the I/O standards (together with their supply and reference voltages) supported by the iCE40 devices.

Input Standard	V _{CCIO} (Typical)					
input Standard	3.3 V	2.5 V	1.8 V			
Single-Ended Interfaces		•				
LVCMOS33	Yes					
LVCMOS25		Yes				
LVCMOS18			Yes			
Differential Interfaces		•				
LVDS251		Yes				
subLVDS ¹			Yes			

Table 2-7. Supported Input Standards

1. Bank 3 only.

Table 2-8. Supported Output Standards

Output Standard	V _{CCIO} (Typical)
Single-Ended Interfaces	
LVCMOS33	3.3
LVCMOS25	2.5
LVCMOS18	1.8
Differential Interfaces	
LVDS25E1	2.5
subLVDSE ¹	1.8

1. These interfaces can be emulated with external resistors in all devices.

Non-Volatile Configuration Memory

All iCE40 devices provide a Non-Volatile Configuration Memory (NVCM) block which can be used to configure the device.

For more information on the NVCM, please refer to TN1248, iCE40 Programming and Configuration Usage Guide.



Power On Reset

iCE40 devices have power-on reset circuitry to monitor V_{CC} , V_{CCIO_2} , V_{PP_2V5} , and V_{CC_SPI} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CC} , V_{CCIO_2} , V_{PP_2V5} , and V_{CC_SPI} (controls configuration) voltage levels. It then triggers download from the on-chip NVCM or external Flash memory after reaching the power-up levels specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration.

Programming and Configuration

This section describes the programming and configuration of the iCE40 family.

Device Programming

The NVCM memory can be programmed through the SPI port.

Device Configuration

There are various ways to configure the Configuration RAM (CRAM) including:

- 1. Internal NVCM Download
- 2. From a SPI Flash (Master SPI mode)
- 3. System microprocessor to drive a Serial Slave SPI port (SSPI mode)

The image to configure the CRAM can be selected by the user on power up (Cold Boot) or once powered up (Warm Boot).

For more details on programming and configuration, see TN1248, iCE40 Programming and Configuration Usage Guide.

Power Saving Options

iCE40 devices are available in two options for maximum flexibility: LP and HX devices. The LP devices have ultra low static and dynamic power consumption. HX devices are designed to provide high performance. Both the LP and the HX devices operate at 1.2 V V_{CC} .

iCE40 devices feature iCEGate and PLL low power mode to allow users to meet the static and dynamic power requirements of their applications. While these features are available in both device types, these features are mainly intended for use with iCE40 LP devices to manage power consumption.

Table 2-9. iCE40 Power Saving Features Description

Device Subsystem	Feature Description
	When LATCHINPUTVALUE is enabled, forces the PLL into low-power mode; PLL output held static at last input clock value.
	To save power, the optional iCEgate latch can selectively freeze the state of individual, non-regis- tered inputs within an I/O bank. Registered inputs are effectively frozen by their associated clock or clock-enable control.



iCE40 LP/HX Family Data Sheet DC and Switching Characteristics

March 2015

Data Sheet DS1040

Absolute Maximum Ratings^{1, 2, 3, 4}

iCE40 LP/HX

Supply Voltage V _{CC}	
Output Supply Voltage V _{CCIO} , V _{CC_SPI} –0.5 V to 3.60 V	
NVCM Supply Voltage V _{PP_2V5}	
PLL Supply Voltage V _{CCPLL} 0.5 V to 1.30 V	
I/O Tri-state Voltage Applied	
Dedicated Input Voltage Applied0.5 V to 3.60 V	
Storage Temperature (Ambient)65 °C to 150 °C	
Junction Temperature (T _J)	

1. Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

2. Compliance with the Lattice Thermal Management document is required.

3. All voltages referenced to GND.

 IOs can support a 200 mV Overshoot above the Recommend Operating Conditions V_{CCIO} (Max) and -200mV Undershoot below V_{IL} (Min). Overshoot and Undershoot is permitted for 25% duty cycle but must not exceed 1.6 ns.

Recommended Operating Conditions¹

Symbol	Param	neter	Min.	Max.	Units
V _{CC} ¹	Core Supply Voltage		1.14	1.26	V
	Slave SPI Configuration	1.71	3.46	V	
V	V _{PP_2V5} NVCM Programming and Operating Supply Voltage	Master SPI Configuration	2.30	3.46	V
V _{PP_2V5}	Operating Supply Voltage	Configure from NVCM	2.30	3.46	V
		NVCM Programming	2.30	3.00	V
V _{PP_FAST} ⁴	Optional fast NVCM programming supply	y. Leave unconnected.	N/A	N/A	V
V _{CCPLL} ^{5, 6}	PLL Supply Voltage		1.14	1.26	V
V _{CCIO} ^{1, 2, 3}	I/O Driver Supply Voltage	V _{CCIO0-3}	1.71	3.46	V
V CCIO	NO Driver Supply Voltage	V _{CC_SPI}	1.71	3.46	V
t _{JIND}	Junction Temperature Industrial Operation		-40	100	°C
t _{PROG}	Junction Temperature NVCM Programm	ing	10	30	°C

1. Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC_SPI} are both the same voltage, they must also be the same supply.

2. See recommended voltages by I/O standard in subsequent table.

3. V_{CCIO} pins of unused I/O banks should be connected to the V_{CC} power supply on boards.

V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.

5. No PLL available on the iCE40LP384 and iCE40LP640 device.

6. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

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Power Supply Ramp Rates^{1, 2}

Symbol	Parameter		Min.	Max.	Units
		All configuration modes. No power supply sequencing.	0.40	10	V/ms
		Configuring from Slave SPI. No power supply sequencing,	0.01	10	V/ms
t _{RAMP}	Power supply ramp rates for all power supplies.	Configuring from NVCM. V_{CC} and $V_{PP_{2V5}}$ to be powered 0.25 ms before $V_{CC_{SPI}}$.	0.01	10	V/ms
		Configuring from MSPI. V_{CC} and V_{PP_SPI} to be powered 0.25 ms before V_{PP_2V5} .	0.01	10	V/ms

1. Assumes monotonic ramp rates.

2. iCE40LP384 requires V_{CC} to be greater than 0.7V when V_{CCIO} and V_{CC_SPI} are above GND.

Power-On-Reset Voltage Levels¹

Symbol	Device	Parameter		Min.	Max.	Units
V _{PORUP}	iCE40LP384	Power-On-Reset ramp-up trip point	VCC	0.67	0.99	V
		(band gap based circuit monitoring VCC, VCCIO_2, VCC_SPI and	VCCIO_2	0.70	1.59	V
		VPP_2V5)	VCC_SPI	0.70	1.59	V
			VPP_2V5	0.70	1.59	V
	iCE40LP640,	Power-On-Reset ramp-up trip point	VCC	0.55	0.75	V
	iCE40LP/HX1K, iCE40LP/HX4K,	, VCC, VCCIO_2, VCC_SPI and	VCCIO_2	0.86	1.29	V
	iCE40LP/HX8K		VCC_SPI	0.86	1.29	V
			VPP_2V5	0.86	1.33	V
V _{PORDN}	iCE40LP384	Power-On-Reset ramp-down trip	VCC	—	0.64	V
		point (band gap based circuit moni- toring VCC, VCCIO_2, VCC_SPI	VCCIO_2	—	1.59	V
		and VPP_2V5)	VCC_SPI	—	1.59	V
			VPP_2V5	—	1.59	V
	iCE40LP640, Power	Power-On-Reset ramp-down trip	VCC	—	0.75	V
	iCE40LP/HX1K, iCE40LP/HX4K,	point (band gap based circuit moni- toring VCC, VCCIO_2, VCC_SPI	VCCIO_2	—	1.29	V
	iCE40LP/HX8K	and VPP_2V5)	VCC_SPI	—	1.29	V
			VPP_2V5	—	1.33	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.

ESD Performance

Please refer to the iCE40 Product Family Qualification Summary for complete qualification data, including ESD performance.



DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
I _{IL,} I _{IH} ^{1, 3, 4, 5, 6, 7}	Input or I/O Leakage	$0V < V_{IN} < V_{CCIO} + 0.2 V$	—	_	+/—10	μA
C ₁ ^{6, 7}	I/O Capacitance ²	$V_{CCIO} = 3.3 V, 2.5 V, 1.8 V$ $V_{CC} = Typ., V_{IO} = 0 to V_{CCIO} + 0.2 V$	_	6	_	pf
C ₂ ^{6, 7}	Global Input Buffer Capacitance ²	$V_{CCIO} = 3.3 V, 2.5 V, 1.8 V$ $V_{CC} = Typ., V_{IO} = 0 to V_{CCIO} + 0.2 V$	_	6	_	pf
V _{HYST}	Input Hysteresis	V _{CCIO} = 1.8 V, 2.5 V, 3.3 V	—	200		mV
I _{PU} ^{6, 7}	Internal PIO Pull-up	$V_{CCIO} = 1.8 \text{ V}, 0 = < V_{IN} < = 0.65 \text{ V}_{CCIO}$	-3		-31	μΑ
	Current	$V_{CCIO} = 2.5 \text{ V}, 0 = < V_{IN} < = 0.65 \text{ V}_{CCIO}$	-8	—	-72	μA
		$V_{CCIO} = 3.3 \text{ V}, 0 = < V_{IN} < = 0.65 \text{ V}_{CCIO}$	-11	—	-128	μA

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Internal pull-up resistors are disabled.

2. T_J 25°C, f = 1.0 MHz.

3. Please refer to VIL and VIH in the sysIO Single-Ended DC Electrical Characteristics table of this document.

4. Only applies to IOs in the SPI bank following configuration.

5. Some products are clamped to a diode when V_{IN} is larger than $V_{\text{CCIO}}.$

6. High current IOs has three sysIO buffers connected together.

7. The iCE40LP640 and iCE40LP1K SWG16 package has CDONE and a sysIO buffer are connected together.

Static Supply Current – LP Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. V _{CC} ⁴	Units
		iCE40LP384	21	μA
		iCE40LP640	100	μA
I _{CC}	Core Power Supply	iCE40LP1K	100	μA
		iCE40LP4K	250	μA
		iCE40LP8K	250	μA
I _{CCPLL} ^{5, 6}	PLL Power Supply	All devices	0.5	μA
I _{PP_2V5}	NVCM Power Supply	All devices	1.0	μA
ICCIO, ICC_SPI	Bank Power Supply⁴ V _{CCIO} = 2.5 V	All devices	3.5	μΑ

1. Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip PLL is off. For more detail with your specific design, use the Power Calculator tool. Power specified with master SPI configuration mode. Other modes may be up to 25% higher.

2. Frequency = 0 MHz.

3. $T_J = 25$ °C, power supplies at nominal voltage.

4. Does not include pull-up.

5. No PLL available on the iCE40LP384 and iCE40LP640 device.

6. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.



Static Supply Current – HX Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. V _{CC} ⁴	Units
		iCE40HX1K	296	μΑ
I _{CC}	Core Power Supply	iCE40HX4K	1140	μA
		iCE40HX8K	1140	μΑ
I _{CCPLL} ⁵	PLL Power Supply	All devices	0.5	μA
I _{PP_2V5}	NVCM Power Supply	All devices	1.0	μΑ
ICCIO, ICC_SPI	Bank Power Supply ⁴ V _{CCIO} = 2.5 V	All devices	3.5	μΑ

Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip PLL is off. For more detail with your specific design, use the Power Calculator tool. Power specified with master SPI configuration mode. Other modes may be up to 25% higher.

2. Frequency = 0 MHz.

3. $T_J = 25 \degree$ C, power supplies at nominal voltage.

4. Does not include pull-up.

5. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

Programming NVCM Supply Current – LP Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. V _{CC} ⁵	Units
		iCE40LP384	60	μA
		iCE40LP640	120	μΑ
I _{CC}	Core Power Supply	iCE40LP1K	120	μΑ
		iCE40LP4K	350	μΑ
		iCE40LP8K	350	μΑ
I _{CCPLL} ^{6, 7}	PLL Power Supply	All devices	0.5	μΑ
I _{PP_2V5}	NVCM Power Supply	All devices	2.5	μA
I _{CCIO⁸, I_{CC_SPI}}	Bank Power Supply ⁵	All devices	3.5	μΑ

1. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.

2. Typical user pattern.

3. SPI programming is at 8 MHz.

4. $T_J = 25$ °C, power supplies at nominal voltage.

5. Per bank. $V_{CCIO} = 2.5$ V. Does not include pull-up.

6. No PLL available on the iCE40-LP384 and iCE40-LP640 device.

7. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

8. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.



Programming NVCM Supply Current – HX Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. V _{CC} ⁵	Units
		iCE40HX1K	278	μΑ
I _{CC}	Core Power Supply	iCE40HX4K	1174	μΑ
		iCE40HX8K	1174	μΑ
I _{CCPLL} ⁶	PLL Power Supply	All devices	0.5	μA
I _{PP_2V5}	NVCM Power Supply	All devices	2.5	mA
I _{CCIO⁷, I_{CC_SPI}}	Bank Power Supply ⁵	All devices	3.5	mA

1. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.

2. Typical user pattern.

3. SPI programming is at 8 MHz.

4. $T_J = 25$ °C, power supplies at nominal voltage.

5. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up.

6. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

7. V_{PP FAST}, used only for fast production programming, must be left floating or unconnected in applications.

Peak Startup Supply Current – LP Devices

Symbol	Parameter	Device	Max	Units
		iCE40LP384	7.7	mA
		iCELP640	6.4	mA
ССРЕАК	Core Power Supply	iCE40LP1K	6.4	mA
		iCE40LP4K	15.7	mA
		iCE40LP8K	15.7	mA
		iCE40LP1K	1.5	mA
ICCPLLPEAK ^{1, 2, 4}	PLL Power Supply	iCELP640	1.5	mA
		iCE40LP4K	8.0	mA
		iCE40LP8K	8.0	mA
		iCE40LP384	3.0	mA
		iCELP640	7.7	mA
I _{PP_2V5PEAK}	NVCM Power Supply	iCE40LP1K	7.7	mA
		iCE40LP4K	4.2	mA
		iCE40LP8K	4.2	mA
		iCE40LP384	5.7	mA
IPP_FASTPEAK ³	NVCM Programming Supply	iCELP640	8.1	mA
		iCE40LP1K	8.1	mA
		iCE40LP384	8.4	mA
		iCELP640	3.3	mA
I _{CCIOPEAK} ⁵ , I _{CC_SPIPEAK}	Bank Power Supply	iCE40LP1K	3.3	mA
		iCE40LP4K	8.2	mA
		iCE40LP8K	8.2	mA

1. No PLL available on the iCE40LP384 and iCE40LP640 device.

2. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

3. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.

4. While no PLL is available in the iCE40-LP640 the I_{CCPLLPEAK} is additive to I_{CCPEAK}.

5. iCE40LP384 requires V_{CC} to be greater than 0.7 V when V_{CCIO} and V_{CC_SPI} are above GND.



Peak Startup Supply Current – HX Devices

Symbol	Parameter	Device	Max	Units	
		iCE40HX1K	6.9	mA	
ІССРЕАК	Core Power Supply	iCE40HX4K	22.3	mA	
		iCE40HX8K	22.3	mA	
		iCE40HX1K	1.8	mA	
I _{CCPLLPEAK} ¹	PLL Power Supply	iCE40HX4K	6.4	mA	
		iCE40HX8K	6.4	mA	
		iCE40HX1K	2.8	mA	
I _{PP_2V5PEAK}	NVCM Power Supply	iCE40HX4K	4.1	mA	
		iCE40HX8K	4.1	mA	
		iCE40HX1K	6.8	mA	
ICCIOPEAK, ICC_SPIPEAK	Bank Power Supply	iCE40HX4K	6.8	mA	
		iCE40HX8K	6.8	mA	

1. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

sysIO Recommended Operating Conditions

	V _{CCIO} (V)		
Standard	Min.	Тур.	Max.
LVCMOS 3.3	3.14	3.3	3.46
LVCMOS 2.5	2.37	2.5	2.62
LVCMOS 1.8	1.71	1.8	1.89
LVDS25E ^{1, 2}	2.37	2.5	2.62
subLVDSE ^{1, 2}	1.71	1.8	1.89

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.

2. Does not apply to Configuration Bank V_{CC_SPI}.

sysIO Single-Ended DC Electrical Characteristics

Input/	V	IL		V _{IH} ¹			1	
Output Standard	Min. (V)	Max. (V)	Min. (V)	Max. (V)	V _{OL} Max. (V)	V _{OH} Min. (V)	I _{OL} Max. (mA)	I _{OH} Max. (mA)
LVCMOS 3.3	-0.3	0.8	2.0	V _{CCIO} + 0.2 V	0.4	$V_{CCIO} - 0.4$	8, 16 ² , 24 ²	-8, -16 ² , -24 ²
EVOINOU 0.0	0.0	0.0	2.0	V CCIO + 0.2 V	0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 2.5	-0.3	0.7	1.7	V _{CCIO} + 0.2 V	0.4	$V_{CCIO} - 0.4$	6, 12 ² , 18 ²	-6, -12 ² , -18 ²
2.0	0.0	0.7	1.7	V CCIO + 0.2 V	0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.8	-0.3	0.35V _{CCIO}	0.65V _{CCIO}		0.4	$V_{CCIO} - 0.4$	4, 8 ² , 12 ²	-4, -8 ² , -12 ²
	-0.5	0.33 A CCIO	0.03 A CCIO	V _{CCIO} + 0.2 V	0.2	$V_{CCIO} - 0.2$	0.1	-0.1

1. Some products are clamped to a diode when V_{IN} is larger than $V_{\text{CCIO.}}$

2. Only for High Drive LED outputs.



sysIO Differential Electrical Characteristics

The LVDS25E/subLVDSE differential output buffers are available on all banks but the LVDS/subLVDS input buffers are only available on Bank 3 of iCE40 devices.

LVDS25

Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Тур.	Max.	Units
V _{INP,} V _{INM}	Input Voltage	$V_{CCIO}^{1} = 2.5$	0	—	2.5	V
V _{THD}	Differential Input Threshold		250	350	450	mV
V _{CM}	Input Common Mode Voltage	$V_{\rm CCIO}^{1} = 2.5$	(V _{CCIO} /2) - 0.3	$V_{CCIO}/2$	$(V_{CCIO}/2) + 0.3$	V
I _{IN}	Input Current	Power on	—	—	±10	μΑ

1. Typical.

subLVDS

Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Тур.	Max.	Units
V _{INP,} V _{INM}	Input Voltage	$V_{CCIO}^{1} = 1.8$	0		1.8	V
V _{THD}	Differential Input Threshold		100	150	200	mV
V _{CM}	Input Common Mode Voltage	$V_{CCIO}^{1} = 1.8$	(V _{CCIO} /2) - 0.25	$V_{CCIO}/2$	$(V_{CCIO}/2) + 0.25$	V
I _{IN}	Input Current	Power on	—		±10	μΑ

1. Typical.



LVDS25E Emulation

iCE40 devices can support LVDSE outputs via emulation on all banks. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS25E standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

Figure 3-1. LVDS25E Using External Resistors

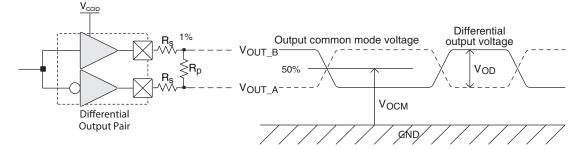


Table 3-1. LVDS25E DC Conditions

Parameter	Description	Тур.	Units
Z _{OUT}	Output impedance	20	Ohms
R _S	Driver series resistor	150	Ohms
R _P	Driver parallel resistor	140	Ohms
R _T	Receiver termination	100	Ohms
V _{OH}	Output high voltage	1.43	V
V _{OL}	Output low voltage	1.07	V
V _{OD}	Output differential voltage	0.30	V
V _{CM}	Output common mode voltage	1.25	V
Z _{BACK}	Back impedance	100.5	Ohms
I _{DC}	DC output current	6.03	mA

Over Recommended Operating Conditions



SubLVDS Emulation

The iCE40 family supports the differential subLVDS standard. The output standard is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all banks of the devices. The sub-LVDS input standard is supported by the LVDS25 differential input buffer. The scheme shown in Figure 3-2 is one possible solution for subLVDSE output standard implementation. Use LVDS25E mode with suggested resistors for subLVDSE operation. Resistor values in Figure 3-2 are industry standard values for 1% resistors.

Figure 3-2. subLVDSE

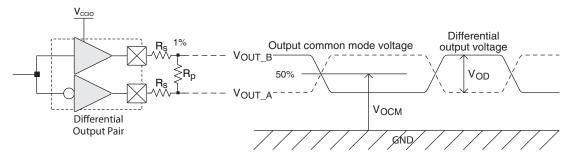


Table 3-2. subLVDSE DC Conditions

Parameter	Description	Тур.	Units
Z _{OUT}	Output impedance	20	Ohms
R _S	Driver series resistor	270	Ohms
R _P	Driver parallel resistor	120	Ohms
R _T	Receiver termination	100	Ohms
V _{OH}	Output high voltage	1.43	V
V _{OL}	Output low voltage	1.07	V
V _{OD}	Output differential voltage	0.35	V
V _{CM}	Output common mode voltage	0.9	V
Z _{BACK}	Back impedance	100.5	Ohms
I _{DC}	DC output current	2.8	mA

Over Recommended Operating Conditions



Typical Building Block Function Performance – LP Devices^{1, 2}

Pin-to-Pin Performance (LVCMOS25)

Function	Timing	Units
Basic Functions		
16-bit decoder	11.0	ns
4:1 MUX	12.0	ns
16:1 MUX	13.0	ns

Register-to-Register Performance

Function	Timing	Units
Basic Functions	· · ·	
16:1 MUX	190	MHz
16-bit adder	160	MHz
16-bit counter	175	MHz
64-bit counter	65	MHz
Embedded Memory Functions		-
256x16 Pseudo-Dual Port RAM	240	MHz

1. The above timing numbers are generated using the iCECube2 design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.

2. Using a V_{CC} of 1.14 V at Junction Temp 85 °C.

Typical Building Block Function Performance – HX Devices^{1, 2}

Pin-to-Pin Performance (LVCMOS25)

Function	Timing	Units
Basic Functions		
16-bit decoder	10.0	ns
4:1 MUX	9.0	ns
16:1 MUX	9.5	ns

Register-to-Register Performance

Function	Timing	Units
Basic Functions		•
16:1 MUX	305	MHz
16-bit adder	220	MHz
16-bit counter	255	MHz
64-bit counter	105	MHz
Embedded Memory Functions		•
256x16 Pseudo-Dual Port RAM	403	MHz

1. The above timing numbers are generated using the iCECube2 design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.

2. Using a V_{CC} of 1.14 V at Junction Temp 85 °C.



Derating Logic Timing

Logic timing provided in the following sections of the data sheet and the Lattice design tools are worst case numbers in the operating range. Actual delays may be much faster. Lattice design tools can provide logic timing numbers at a particular temperature and voltage.

Maximum sysIO Buffer Performance²

I/O Standard	Max. Speed	Units
	Inputs	
LVDS251	400	MHz
subLVDS18 ¹	400	MHz
LVCMOS33	250	MHz
LVCMOS25	250	MHz
LVCMOS18	250	MHz
	Outputs	
LVDS25E	250	MHz
subLVDS18E	155	MHz
LVCMOS33	250	MHz
LVCMOS25	250	MHz
LVCMOS18	155	MHz

1. Supported in Bank 3 only.

2. Measured with a toggling pattern

iCE40 Family Timing Adders

Over Recommended Commercial Operating Conditions - LP Devices^{1, 2, 3, 4, 5}

Buffer Type	Description	Timing	Units
Input Adjusters	I		
LVDS25	LVDS, $V_{CCIO} = 2.5 V$	-0.18	ns
subLVDS	subLVDS, V _{CCIO} = 1.8 V	0.82	ns
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	0.18	ns
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	0.19	ns
Output Adjusters			
LVDS25E	LVDS, Emulated, V _{CCIO} = 2.5 V	0.00	ns
subLVDSE	subLVDS, Emulated, V _{CCIO} = 1.8 V	1.32	ns
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	-0.12	ns
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	1.32	ns

1. Timing adders are relative to LVCMOS25 and characterized but not tested on every device.

2. LVCMOS timing measured with the load specified in Switching Test Condition table.

3. All other standards tested according to the appropriate specifications.

4. Commercial timing numbers are shown.

5. Not all I/O standards are supported for all banks. See the Architecture section of this data sheet for details.



Over Recommended Commercial Operating Conditions - HX Devices^{1, 2, 3, 4, 5}

Buffer Type	Description	Timing	Units
Input Adjusters	I		
LVDS25	LVDS, $V_{CCIO} = 2.5 V$	0.13	ns
subLVDS	subLVDS, V _{CCIO} = 1.8 V	1.03	ns
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	0.16	ns
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	0.23	ns
Output Adjusters	· · ·		
LVDS25E	LVDS, Emulated, V _{CCIO} = 2.5 V	0.00	ns
subLVDSE	subLVDS, Emulated, V _{CCIO} = 1.8 V	1.76	ns
LVCMOS33	LVCMOS, V _{CCIO} = 3.3 V	0.17	ns
LVCMOS25	LVCMOS, V _{CCIO} = 2.5 V	0.00	ns
LVCMOS18	LVCMOS, V _{CCIO} = 1.8 V	1.76	ns

1. Timing adders are relative to LVCMOS25 and characterized but not tested on every device.

2. LVCMOS timing measured with the load specified in Switching Test Condition table.

3. All other standards tested according to the appropriate specifications.

4. Commercial timing numbers are shown.

5. Not all I/O standards are supported for all banks. See the Architecture section of this data sheet for details.



iCE40 External Switching Characteristics – LP Devices ^{1, 2}

Over Recommended Operating Conditions

Parameter	Description	Device	Min.	Max.	Units
Clocks					
Global Clocks					
f _{MAX_GBUF}	Frequency for Global Buffer Clock network	All iCE40LP devices	—	275	MHz
t _{W_GBUF}	Clock Pulse Width for Global Buffer	All iCE40LP devices	0.92	—	ns
		iCE40LP384	-	370	ps
		iCE40LP640	-	230	ps
t _{SKEW_GBUF}	Global Buffer Clock Skew Within a Device	iCE40LP1K	-	230	ps
		iCE40LP4K	-	340	ps
		iCE40LP8K	-	340	ps
Pin-LUT-Pin Propa	agation Delay			1	1
t _{PD}	Best case propagation delay through one LUT-4	All iCE40LP devices	—	9.36	ns
General I/O Pin Pa	rameters (Using Global Buffer Clock withou	it PLL) ³			
		iCE40LP384	_	300	ps
		iCE40LP640	—	200	ps
t _{SKEW_} IO	Data bus skew across a bank of IOs	iCE40LP1K		200	ps
		iCE40LP4K		280	ps
		iCE40LP8K		280	ps
		iCE40LP384		6.33	ns
		iCE40LP640		5.91	ns
t _{co}	Clock to Output - PIO Output Register	iCE40LP1K		5.91	ns
		iCE40LP4K		6.58	ns
		iCE40LP8K		6.58	ns
		iCE40LP384	-0.08	_	ns
		iCE40LP640	-0.33	_	ns
t _{SU}	Clock to Data Setup - PIO Input Register	iCE40LP1K	-0.33	_	ns
		iCE40LP4K	-0.63	_	ns
		iCE40LP8K	-0.63	_	ns
		iCE40LP384	1.99	_	ns
		iCE40LP640	2.81	_	ns
t _H	Clock to Data Hold - PIO Input Register	iCE40LP1K	2.81	_	ns
		iCE40LP4K	3.48	—	ns
		iCE40LP8K	3.48	—	ns
General I/O Pin Pa	arameters (Using Global Buffer Clock with P	LL) ³	I	1	1
		iCE40LP1K	_	2.20	ns
t _{COPLL}	Clock to Output - PIO Output Register	iCE40LP4K		2.30	ns
		iCE40LP8K	— —	2.30	ns
		iCE40LP1K	5.23	—	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	iCE40LP4K	6.13	—	ns
		iCE40LP8K	6.13		ns



iCE40 External Switching Characteristics – LP Devices (Continued)^{1, 2}

Over Recommended Operating Conditions

Parameter	Description	Device	Min.	Max.	Units
t _{HPLL}		iCE40LP1K	-0.90	_	ns
		iCE40LP4K	-0.80	_	ns
		iCE40LP8K	-0.80		ns

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions can be extracted from the iCECube2 software.

2. General I/O timing numbers based on LVCMOS 2.5, 0pf load.

3. Supported on devices with a PLL.



iCE40 External Switching Characteristics – HX Devices ^{1, 2}

Over Recommended Operating Conditions

Parameter	Description	Device	Min.	Max.	Units
Clocks					
Primary Clocks					
f _{MAX_GBUF}	Frequency for Global Buffer Clock network	All iCE40HX devices	_	275	MHz
t _{W_GBUF}	Clock Pulse Width for Global Buffer	All iCE40HX devices	0.88	—	ns
		iCE40HX1K	—	727	ps
t _{SKEW_GBUF}	Global Buffer Clock Skew Within a Device	iCE40HX4K	—	300	ps
		iCE40HX8K	—	300	ps
Pin-LUT-Pin Prop	agation Delay	•			1
t _{PD}	Best case propagation delay through one LUT-4	All iCE40 HX devices	_	7.30	ns
General I/O Pin P	arameters (Using Global Buffer Clock witho	ut PLL)		•	
		iCE40HX1K	—	696	ps
t _{SKEW_IO}	Data bus skew across a bank of IOs	iCE40HX4K	—	290	ps
		iCE40HX8K	—	290	ps
		iCE40HX1K	—	5.00	ns
t _{co}	Clock to Output - PIO Output Register	iCE40HX4K	—	5.41	ns
		iCE40HX8K	—	5.41	ns
		iCE40HX1K	-0.23	—	ns
t _{SU}	Clock to Data Setup - PIO Input Register	iCE40HX4K	-0.43	—	ns
		iCE40HX8K	-0.43	—	ns
		iCE40HX1K	1.92	—	ns
t _H	Clock to Data Hold - PIO Input Register	iCE40HX4K	2.38	—	ns
		iCE40HX8K	2.38	—	ns
General I/O Pin P	arameters (Using Global Buffer Clock with I	PLL) ³			
		iCE40HX1K	—	2.96	ns
t _{COPLL}	Clock to Output - PIO Output Register	iCE40HX4K	—	2.51	ns
		iCE40HX8K	—	2.51	ns
		iCE40HX1K	3.10	—	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	iCE40HX4K	4.16	—	ns
		iCE40HX8K	4.16	—	ns
		iCE40HX1K	-0.60	—	ns
t _{HPLL}	Clock to Data Hold - PIO Input Register	iCE40HX4K	-0.53	_	ns
		iCE40HX8K	-0.53	—	ns

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the iCECube2 software.

2. General I/O timing numbers based on LVCMOS 2.5, 0pf load.

3. Supported on devices with a PLL.



sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Min.	Max.	Units
f _{IN}	Input Clock Frequency (REFERENCECLK, EXTFEEDBACK)		10	133	MHz
f _{OUT}	Output Clock Frequency (PLLOUT)		16	275	MHz
f _{VCO}	PLL VCO Frequency		533	1066	MHz
f _{PFD}	Phase Detector Input Frequency		10	133	MHz
AC Characteris	tics				
+	Output Clock Duty Cycle	f _{OUT} < 175 MHz. Without duty trim selected	40	50	%
t _{DT}		175 MHz < f _{OUT} < 275 MHz. Without duty trim selected	35	65	"%
t _{PH}	Output Phase Accuracy			+/-12	deg
	Output Clock Period Jitter	f _{OUT} <= 100 MHz		450	ps p-p
	Oulput Clock Period Siller	f _{OUT} > 100 MHz	_	0.05	UIPP
t _{OPJIT} ^{1, 5}	Output Clock Cycle-to-cycle Jitter	f _{OUT} <= 100 MHz	—	750	ps p-p
	Output Clock Cycle-to-cycle Sitter	f _{OUT} > 100 MHz	—	0.10	UIPP
	Output Clock Phase Jitter	f _{PFD} <= 25 MHz	_	275	ps p-p
	Ouput Clock Fhase Siller	f _{PFD} > 25 MHz		0.05	UIPP
t _W	Output Clock Pulse Width	At 90% or 10%	1.3	—	ns
t _{LOCK} ^{2, 3}	PLL Lock-in Time		_	50	us
t _{UNLOCK}	PLL Unlock Time			50	ns
t _{IPJIT} ⁴	Input Clock Period Jitter	$f_{PFD} \ge 20 \text{ MHz}$		1000	ps p-p
ЧРЈІТ	Input Clock Feriod Siller	f _{PFD} < 20 MHz	_	0.02	UIPP
t _{FDTAP}	Fine Delay adjustment, per Tap		147	195	ps
t _{STABLE} ³	LATCHINPUTVALUE LOW to PLL Stable		_	500	ns
t _{STABLE_PW} ³	LATCHINPUTVALUE Pulse Width		—	100	ns
t _{RST}	RESET Pulse Width		10	—	ns
t _{RSTREC}	RESET Recovery Time		10		us
t _{DYNAMIC_WD}	DYNAMICDELAY Pulse Width		100		VCO Cycles
t	Propagation delay with the PLL in bypass	iCE40LP	1.18	4.68	ns
t _{PDBYPASS}	mode	iCE40HX	1.73	4.07	ns

1. Period jitter sample is taken over 10,000 samples of the primary PLL output with a clean reference clock. Cycle-to-cycle jitter is taken over 1000 cycles. Phase jitter is taken over 2000 cycles. All values per JESD65B.

2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.

3. At minimum f_{PFD} . As the f_{PFD} increases the time will decrease to approximately 60% the value listed.

4. Maximum limit to prevent PLL unlock from occurring. Does not imply the PLL will operate within the output specifications listed in this table.

5. The jitter values will increase with loading of the PLD fabric and in the presence of SSO noise.



SPI Master or NVCM Configuration Time^{1, 2}

Symbol	Parameter	Conditions	Тур.	Units
		iCE40LP384 - Low Frequency (Default)	25	ms
		iCE40LP384 - Medium Frequency	15	ms
		iCE40LP384 - High Frequency	11	ms
		iCE40LP640 - Low Frequency (Default)	53	ms
		iCE40LP640 - Medium Frequency	25	ms
		iCE40LP640 - High Frequency	13	ms
		iCE40LP/HX1K - Low Frequency (Default)	53	ms
t _{CONFIG}	POR/CRESET_B to Device I/O Active	iCE40LP/HX1K - Medium Frequency	25	ms
		iCE40LP/HX1K - High Frequency	13	ms
		iCE40LP/HX4K - Low Frequency (Default)	230	ms
		iCE40LP/HX4K - Medium Frequency	110	ms
		iCE40LP/HX4K - High Frequency	70	ms
		iCE40LP/HX8K - Low Frequency (Default)	230	ms
		iCE40LP/HX8K - Medium Frequency	110	ms
		iCE40LP/HX8K - High Frequency	70	ms

1. Assumes sysMEM Block is initialized to an all zero pattern if they are used.

2. The NVCM download time is measured with a fast ramp rate starting from the maximum voltage of POR trip point.



sysCONFIG Port Timing Specifications¹

Symbol	Parameter		Min.	Тур.	Max.	Units
All Configuration	on Modes	1		1		
t _{CRESET_B}	Minimum CRESET_B Low pulse width required to restart configu- ration, from falling edge to rising edge		200	—	_	ns
t _{DONE_IO}	Number of configuration clock cycles after CDONE goes High before the PIO pins are activated		49		_	Clock Cycles
Slave SPI				•		•
	Minimum time from a rising edge	iCE40LP384	600	-	—	us
t _{CR_SCK}	on CRESET_B until the first SPI write operation, first SPI_SCK. During this time, the iCE40	iCE40LP640, iCE40LP/HX1K	800	-	—	us
	device is clearing its internal con-	iCE40LP/HX4K	1200	-	—	us
	figuration memory	iCE40LP/HX8K	1200	-	—	us
		Write	1	-	25	MHz
		Read iCE40LP384 ²	-	15	-	MHz
f _{MAX} ¹	CCLK clock frequency	Read iCE40LP640, iCE40LP/HX1K ²	-	15	-	MHz
'MAX		Read iCE40LP/ HX4K ²	-	15	-	MHz
		Read iCE40LP/ HX8K ²	-	15	-	MHz
t _{CCLKH}	CCLK clock pulse width high		20	—	—	ns
t _{CCLKL}	CCLK clock pulse width low		20	—	—	ns
t _{STSU}	CCLK setup time		12		—	ns
t _{STH}	CCLK hold time		12		—	ns
t _{STCO}	CCLK falling edge to valid output		13		-	ns
Master SPI						
		Off	_	0		MHz
f _{MCLK}	MCLK clock frequency	Low Frequency (Default)	_	7.5		MHz
		Medium Frequency ³		24	—	MHz
		High Frequency ³	—	40	_	MHz



sysCONFIG Port Timing Specifications¹ (Continued)

Symbol	Parameter		Min.	Тур.	Max.	Units
		iCE40LP384 - Low Frequency (Default)	600	_	—	us
		iCE40LP384 - Medium Frequency	600	_	—	us
		iCE40LP384 - High Frequency	600	_	—	us
		iCE40LP640, iCE40LP/HX1K - Low Frequency (Default)	800	_	_	us
		iCE40LP640, iCE40LP/HX1K - Medium Frequency	800	_	_	us
		iCE40LP640, iCE40LP/HX1K - High Frequency	800		_	us
	CRESET_B high to first MCLK	iCE40LP/HX1K-Low Frequency (Default)	800	_	—	us
^I MCLK	edge	iCE40LP/HX1K - Medium Frequency	800	_	—	us
		iCE40LP/HX1K - High Frequency	800	_	—	us
		iCE40LP/HX4K - Low Frequency (Default)	1200		—	us
		iCE40LP/HX4K - Medium Frequency	1200	_	—	us
		iCE40LP/HX4K - high frequency	1200	_	—	US
		iCE40LP/HX8K - Low Frequency (Default)	1200	_	—	us
		iCE40LP/HX8K - Medium Frequency	1200		—	us
		iCE40LP/HX8K - High Frequency	1200			us

Does not apply for NVCM.
 Supported only with 1.2 V V_{CC} and at 25 °C.
 Extended range f_{MAX} Write operations support up to 53 MHz only with 1.2 V V_{CC} and at 25 °C.



Switching Test Conditions

Figure 3-3 shows the output test load used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-3.

Figure 3-3. Output Test Load, LVCMOS Standards

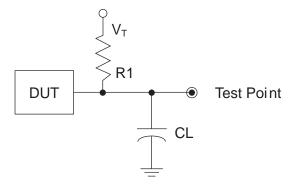


Table 3-3. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R ₁	CL	Timing Reference	V _T
			LVCMOS 3.3 = 1.5 V	—
LVCMOS settings (L -> H, H -> L)	×	0 pF	LVCMOS 2.5 = $V_{CCIO}/2$	—
			LVCMOS 1.8 = $V_{CCIO}/2$	—
LVCMOS 3.3 (Z -> H)			1.5	V _{OL}
LVCMOS 3.3 (Z -> L)			1.5	V _{OH}
Other LVCMOS (Z -> H)	188	0 pF	V _{CCIO} /2	V _{OL}
Other LVCMOS (Z -> L)	100	0 pr	V _{CCIO} /2	V _{OH}
LVCMOS (H -> Z)			V _{OH} - 0.15	V _{OL}
LVCMOS (L -> Z)			V _{OL} - 0.15	V _{OH}

Note: Output test conditions for all other interfaces are determined by the respective standards.



iCE40 LP/HX Family Data Sheet Pinout Information

July 2014

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Signal Descriptions

Signal Name	I/O	Descriptions
General Purpose		
IO[Bank]_[Row/Column Number][A/B]	I/O	[Bank] indicates the bank of the device on which the pad is located. [Number] indicates IO number on the device.
IO[Bank]_[Row/Column Number][A/B]	I/O	[Bank] indicates the bank of the device on which the pad is located. [Number] indicates IO number on the device. [A/B] indicates the differential I/O. 'A' = negative input. 'B' = positive input.
HCIO[Bank]_[Number]	I/O	High Current IO. [Bank] indicates the bank of the device on which the pad is located. [Number] indicates IO number.
NC	—	No connect
GND	—	GND – Ground. Dedicated pins. It is recommended that all GNDs are tied together.
VCC	_	VCC – The power supply pins for core logic. Dedicated pins. It is recommended that all VCCs are tied to the same supply.
VCCIO_x	_	VCCIO – The power supply pins for I/O Bank x. Dedicated pins. All VCCIOs located in the same bank are tied to the same supply.
PLL and Global Functions (Used as u	ser-programmable I/O pins when not used for PLL or clock pins)
VCCPLLx	—	PLL VCC – Power. Dedicated pins. The PLL requires a separate power and ground that is quiet and stable to reduce the output clock jitter of the PLL.
GNDPLLx	_	PLL GND – Ground. Dedicated pins. The sysCLOCK PLL has the DC ground con- nection made on the FPGA, so the external PLL ground connection (GNDPLL) must NOT be connected to the board's ground.
GBINx	—	Global pads. Two per side.
Programming and Configur	ation	
CBSEL[0:1]	I/O	Dual function pins. I/Os when not used as CBSEL. Optional ColdBoot configuration SELect input, if ColdBoot mode is enabled.
CRESET_B	I	Configuration Reset, active Low. Dedicated input. No internal pull-up resistor. Either actively drive externally or connect a 10 KOhm pull-up resistor to VCCIO_2.
CDONE	I/O	Configuration Done. Includes a permanent weak pull-up resistor to VCCIO_2. If driv- ing external devices with CDONE output, an external pull-up resistor to VCCIO_2 may be required. Refer to the TN1248, iCE40 Programming and Configuration for more details. Following device configuration the iCE40LP640 and iCE40LP1K in the SWG16 package CDONE pin can be used as a user output.
VCC_SPI	_	SPI interface voltage supply input. Must have a valid voltage even if configuring from NVCM.
SPI_SCK	I/O	Input Configuration Clock for configuring an FPGA in Slave SPI mode. Output Config- uration Clock for configuring an FPGA configuration modes.
SPI_SS_B	I/O	SPI Slave Select. Active Low. Includes an internal weak pull-up resistor to VCC_SPI during configuration. During configuration, the logic level sampled on this pin determines the configuration mode used by the iCE40 device. An input when sampled at the start of configuration. An input when in SPI Peripheral configuration mode (SPI_SS_B = Low). An output when in Master SPI Flash configuration mode.
SPI_SI	I/O	Slave SPI serial data input and master SPI serial data output
SPI_SO	I/O	Slave SPI serial data output and master SPI serial data input

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Signal Descriptions (Cont.)

Signal Name	I/O	Descriptions
VPP_FAST		Optional fast NVCM programming supply. V _{PP_FAST} , used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V _{PP_FAST} ball connected to V _{CCIO_0} ball externally.
VPP_2V5	—	VPP_2V5 NVCM programming and operating supply



Pin Information Summary

	i	CE40LP38	4	iCE40LP640				iCE4	0LP1K			
	SG32	CM36 ²	CM49 ²	SWG16	SWG16	CM36 ^{1, 2}	CM49 ^{1, 2}	CM81	CB81	QN84	CM121	CB121
General Purpose I/O per Ban	k									•		
Bank 0	6	4	10	3	3	4	10	17	17	17	24	24
Bank 1	5	7	7	0	0	7	7	15	16	17	25	21
Bank 2	0	4	4	1	1	4	4	11	8	11	18	19
Bank 3	6	6	12	2	2	6	10	16	17	18	24	24
Configuration	4	4	4	4	4	4	4	4	4	4	4	4
Total General Purpose Single Ended I/O	21	25	37	10	10	25	35	63	62	67	95	92
High Current Outputs per Ba	ink										•	
Bank 0	0	0	0	3	3	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0	0	0	0
Bank 3	0	0	0	0	0	0	0	0	0	0	0	0
Total Current Outputs	0	0	0	3	3	0	0	0	0	0	0	0
Differential Inputs per Bank												
Bank 0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0	0	0	0
Bank 3	3	3	6	1	1	3	5	8	9	7	12	12
Total Differential Inputs	3	3	6	1	1	3	5	8	9	7	12	12
Dedicated Inputs per Bank												
Bank 0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	2	2	2	1	1	2	2	2	2	2	2	2
Bank 3	0	0	0	0	0	0	0	0	0	0	0	0
Configuration	0	0	0	0	0	0	0	0	0	0	0	0
Total Dedicated Inputs	2	2	2	1	1	2	2	2	2	2	2	2
Vccio Pins												
Bank 0	1	1	1	1	1	1	1	1	1	1	2	1
Bank 1	1	1	1	0	0	0	0	1	1	1	2	1
Bank 2	1	1	1	1	1	1	1	1	1	1	2	1
Bank 3	1	0	0	0	0	0	0	1	1	1	2	2
VCC	1	1	2	1	1	1	2	3	3	4	4	4
VCC_SPI	1	1	1	0	0	1	1	1	1	1	1	1
VPP_2V5	1	1	1	0	0	1	1	1	1	1	1	1
VPP_FAST ³	0	0	0	0	0	1	1	1	0	1	1	1
VCCPLL	0	0	0	0	0	0	1	1	0	0	1	1
GND	2	3	3	2	2	3	4	5	8	4	8	11
NC	0	0	0	0	0	0	0	0	0	0	0	3
Total Count of Bonded Pins	32	36	49	16	16	36	49	81	81	84	121	121

V_{CCIO2} and V_{CCIO1} are connected together.
 V_{CCIO2} and V_{CCIO3} are connected together.
 V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.



Pin Information Summary, Continued

	i	CE40LP4	к	i	CE40LP8	к	i	CE40HX1	к	iCE40HX4K		iCE40HX8K		
	CM81	CM121	CM225	CM81	CM121	CM225	VQ100	CB132	TQ144	CB132	TQ144	CB132	CM225	CT256
General Purpose I/O per	Bank													
Bank 0	17	23	46	17	23	46	19	24	23	24	27	24	46	52
Bank 1	15	21	42	15	21	42	19	25	25	25	29	25	42	52
Bank 2	9	19	40	9	19	40	12	20	20	18	19	18	40	46
Bank 3	18	26	46	18	26	46	18	22	24	24	28	24	46	52
Configuration	4	4	4	4	4	4	4	4	4	4	4	4	4	4
Total General Purpose Single Ended I/O	63	93	178	63	93	178	72	95	96	95	107	95	178	206
High Current Outputs pe	er Bank													
Bank 0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 3	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Total Differential Inputs	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Differential Inputs per B	ank													
Bank 0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 3	9	13	23	9	13	23	9	11	12	12	14	12	23	26
Total Differential Inputs	9	13	23	9	13	23	9	11	12	12	14	12	23	26
Dedicated Inputs per Ba	nk	•						•	•	•				
Bank 0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	1	0	0	1	0	1	1	1	1	1	1	1
Bank 2	2	2	2	2	2	2	2	2	2	2	2	2	2	2
Bank 3	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Configuration	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Total Dedicated Inputs	2	2	3	2	2	3	2	3	3	3	3	3	3	3
Vccio Pins														
Bank 0	1	1	3	1	1	3	2	2	2	2	2	2	3	4
Bank 1	1	1	3	1	1	3	2	2	2	2	2	2	3	4
Bank 2	1	1	3	1	1	3	2	2	2	2	2	2	3	4
Bank 3	1	2	4	1	2	4	3	3	2	3	2	3	4	4
VCC	3	4	8	3	4	8	4	5	4	5	4	5	8	6
VCC_SPI	1	1	1	1	1	1	1	1	1	1	1	1	1	1
VPP_2V5	1	1	1	1	1	1	1	1	1	1	1	1	1	1
VPP_FAST ¹	1	1	1	1	1	1	1	1	1	1	1	1	1	1
VCCPLL	1	2	2	1	2	2	0	1	1	2	2	2	2	2
GND	5	12	18	5	12	18	10	14	10	15	11	15	18	20
NC	0	0	0	0	0	0	0	2	19	0	6	0	0	0
Total Count of Bonded Pins	81	121	225	81	121	225	100	132	144	132	144	132	225	256

1. V_{PP_FAST}, used only for fast production programming, must be left floating or unconnected in applications.



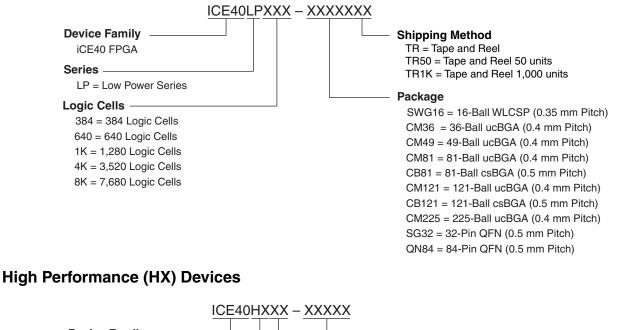
iCE40 LP/HX Family Data Sheet Ordering Information

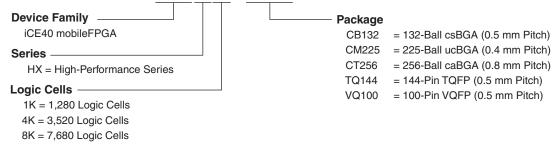
April 2014

Data Sheet DS1040

iCE40 Part Number Description

Ultra Low Power (LP) Devices





All parts shipped in trays unless noted.

Ordering Information

iCE40 devices have top-side markings as shown below:



Note: Markings are abbreviated for small packages.

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Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40LP384-CM36	384	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP384-CM36TR	384	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP384-CM36TR1K	384	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP384-CM49	384	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP384-CM49TR	384	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP384-CM49TR1K	384	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP384-SG32	384	1.2 V	Halogen-Free QFN	32	IND
ICE40LP384-SG32TR	384	1.2 V	Halogen-Free QFN	32	IND
ICE40LP384-SG32TR1K	384	1.2 V	Halogen-Free QFN	32	IND
ICE40LP640-SWG16TR	640	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP640-SWG16TR50	640	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP640-SWG16TR1K	640	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP1K-SWG16TR	1280	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP1K-SWG16TR50	1280	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP1K-SWG16TR1K	1280	1.2 V	Halogen-Free WLCSP	16	IND
ICE40LP1K-CM36	1280	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP1K-CM36TR	1280	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP1K-CM36TR1K	1280	1.2 V	Halogen-Free ucBGA	36	IND
ICE40LP1K-CM49	1280	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP1K-CM49TR	1280	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP1K-CM49TR1K	1280	1.2 V	Halogen-Free ucBGA	49	IND
ICE40LP1K-CM81	1280	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP1K-CM81TR	1280	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP1K-CM81TR1K	1280	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP1K-CB81	1280	1.2 V	Halogen-Free csBGA	81	IND
ICE40LP1K-CB81TR	1280	1.2 V	Halogen-Free csBGA	81	IND
ICE40LP1K-CB81TR1K	1280	1.2 V	Halogen-Free csBGA	81	IND
ICE40LP1K-CM121	1280	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP1K-CM121TR	1280	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP1K-CM121TR1K	1280	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP1K-CB121	1280	1.2 V	Halogen-Free csBGA	121	IND
ICE40LP1K-QN84	1280	1.2 V	Halogen-Free QFN	84	IND
ICE40LP4K-CM81	3520	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP4K-CM81TR	3520	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP4K-CM81TR1K	3520	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP4K-CM121	3520	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP4K-CM121TR	3520	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP4K-CM121TR1K	3520	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP4K-CM225	3520	1.2 V	Halogen-Free ucBGA	225	IND
ICE40LP8K-CM81	7680	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP8K-CM81TR	7680	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP8K-CM81TR1K	7680	1.2 V	Halogen-Free ucBGA	81	IND
ICE40LP8K-CM121	7680	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP8K-CM121TR	7680	1.2 V	Halogen-Free ucBGA	121	IND



Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40LP8K-CM121TR1K	7680	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP8K-CM225	7680	1.2 V	Halogen-Free ucBGA	225	IND

High-Performance Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40HX1K-CB132	1280	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX1K-VQ100	1280	1.2 V	Halogen-Free VQFP	100	IND
ICE40HX1K-TQ144	1280	1.2 V	Halogen-Free TQFP	144	IND
ICE40HX4K-CB132	3520	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX4K-TQ144	3520	1.2 V	Halogen-Free TQFP	144	IND
ICE40HX8K-CB132	7680	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX8K-CM225	7680	1.2 V	Halogen-Free ucBGA	225	IND
ICE40HX8K-CT256	7680	1.2 V	Halogen-Free caBGA	256	IND



iCE40 LP/HX Family Data Sheet Supplemental Information

March 2013

Data Sheet DS1040

For Further Information

A variety of technical notes for the iCE40 family are available on the Lattice web site.

- TN1248, iCE40 Programming and Configuration
- TN1250, Memory Usage Guide for iCE40 Devices
- TN1251, iCE40 sysCLOCK PLL Design and Usage Guide
- TN1252, iCE40 Hardware Checklist
- TN1253, Using Differential I/O (LVDS, Sub-LVDS) in iCE40 Devices
- TN1074, PCB Layout Recommendations for BGA Packages
- iCE40 Pinout Files
- Thermal Management document
- Lattice design tools
- IBIS
- Package Data Sheet
- Schematic Symbols

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iCE40 LP/HX Family Data Sheet Revision History

March 2015

Data Sheet DS1040

Date	Version	Section	Change Summary
March 2015	3.1	DC and Switching Characteristics	Updated sysIO Single-Ended DC Electrical Characteristics section. Changed LVCMOS 3.3 and LVCMOS 2. 5 V _{OH} Min. (V) from 0.5 to 0.4.
July 2014 3.0		DC and Switching Characteristics	Revised and/or added Typ. V _{CC} data in the following sections. Static Supply Current – LP Devices Static Supply Current – HX Devices Programming NVCM Supply Current – LP Devices Programming NVCM Supply Current – HX Devices In each section table, the footnote indicating Advanced device status
		Pinout Information	was removed. Updated Pin Information Summary section. Added footnote 1 to CM49 under iCE40LP1K.
April 2014	02.9	Ordering Information	Changed "i" to "l" in part number description and ordering part numbers.
		Ŭ	Added part numbers to the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging table.
February 2014	02.8	2.8 Introduction	Updated Features section. — Corrected standby power units. — Included High Current LED Drivers
			Updated Table 1-1, iCE40 Family Selection Guide. — Removed LP384 Programmable I/O for 81 ucBGA package.
		Architecture	Updated Supported Standards section. Added information on High Current LED drivers.
		DC and Switching Characteristics	Corrected typos.
			Added footnote to the Peak Startup Supply Current – LP Devices table.
		Ordering Information	Updated part number description in the Ultra Low Power (LP) Devices section.
			Added part numbers to the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging table.
October 2013	02.7	Introduction	Updated Features list and iCE40 Family Selection Guide table.
		Architecture	Revised iCE40-1K device to iCE40LP/HX1K device.
		DC and Switching Characteristics	Added iCE40LP640 device information.
		Pinout Information	Added iCE40LP640 and iCE40LP1K information.
		Ordering Information	Added iCE40LP640 and iCE40LP1K information.
September 2013	02.6	DC and Switching	Updated Absolute Maximum Ratings section.
		Characteristics	Updated sysCLOCK PLL Timing – Preliminary table.
		Pinout Information	Updated Pin Information Summary table.

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Date	Version	Section	Change Summary
August 2013	02.5	Introduction	Updated the iCE40 Family Selection Guide table.
		DC and Switching Characteristics	Updated the following tables: — Absolute Maximum Ratings — Power-On-Reset Voltage Levels — Static Supply Current – LP Devices — Static Supply Current – HX Devices — Programming NVCM Supply Current – LP Devices — Programming NVCM Supply Current – HX Devices — Peak Startup Supply Current – LP Devices — syslO Recommended Operating Conditions — Typical Building Block Function Performance – HX Devices — iCE40 External Switching Characteristics – HX Devices — sysCLOCK PLL Timing – Preliminary — SPI Master or NVCM Configuration Time
		Pinout Information	Updated the Pin Information Summary table.
July 2013	02.4	Introduction	Updated the iCE40 Family Selection Guide table.
		DC and Switching Characteristics	Updated the sysCONFIG Port Timing Specifications table.
		Characteristics	Updated footnote in DC Electrical Characteristics table.
			GDDR tables removed. Support to be provided in a technical note.
		Pinout Information	Updated the Pin Information Summary table.
		Ordering Information	Updated the top-side markings figure.
			Updated the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging table.
May 2013	02.3	DC and Switching Characteristics	Added new data from Characterization.
April 2013	02.2	Introduction	Added the LP8K 81 ucBGA.
		Architecture	Corrected typos.
		DC and Switching Characteristics	Corrected typos. Added 7:1 LVDS waveforms.
		Pinout Information	Corrected typos in signal descriptions. Added the LP8K 81 ucBGA.
		Ordering Information	Added the LP8K 81 ucBGA.
March 2013	02.1	DC and Switching	Recommended operating conditions added requirement for Master SPI.
		Characteristics	Updated Recommended Operating Conditions for V _{PP_2V5} .
			Updated Power-On-Reset Voltage Levels and sequence requirements.
			Updated Static Supply Current conditions.
			Changed unit for t _{SKEW_IO} from ns to ps.
			Updated range of CCLK f _{MAX} .
		Ordering Information	Updated ordering information to include tape and reel part numbers.
September 2012	02.0	—	Merged SiliconBlue iCE40 LP and HX data sheets and updated to Lat- tice format.
	01.31	—	Updated Table 1.
	01.3	—	Production release.
			Updated notes on Table 3: Recommended Operating Conditions.
			Updated values in Table 4, Table 5, Table 12, Table 13 and Table 17.
	01.21	—	Updated Figure 3 and Figure 4 to specify iCE40.
Aug 2012	01.2	—	Updated company name.



Revision History iCE40 LP/HX Family Data Sheet

Date	Version	Section	Change Summary	
July 2011	01.1	_	Moved package specifications to iCE40 pinout Excel files.	
			Updated Table 1 maximum I/Os.	
	01.01	_	Added 640, 1K and 4K to Table 13 configuration times. Updated Table 1 maximum I/Os.	
	01.0		Initial release.	





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